

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)			
- 30	0.004 at V _{GS} = - 10 V	- 120	130 nC			
- 30	0.006 at $V_{GS} = -4.5 \text{ V}$	- 100	130 110			

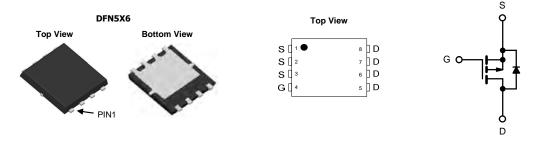
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g Tested



APPLICATIONS

- Notebook
 - Load Switch



P-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 30	V		
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 \text{ °C}$ $T_{C} = 70 \text{ °C}$ $T_{A} = 25 \text{ °C}$ $T_{A} = 70 \text{ °C}$	I _D	- 120 ^a - 100 ^a - 31.6 ^{b, c} - 25.3 ^{b, c}		
Pulsed Drain Current		I _{DM}	- 360	A	
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	- 80 ^a - 56 ^{b, c}		
Single Pulse Avalanche Current L = 0		I _{AS}	- 60		
Single Pulse Avalanche Energy	L = 0.111111	E _{AS}	160	mJ	
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P _D	110 83 6.95 ^{b, c} 5.0 ^{b, c}	w	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	00		
Soldering Recommendations (Peak Temperature		260	- ℃		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	15	20	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	0.9	1.2	C/VV	

Notes:

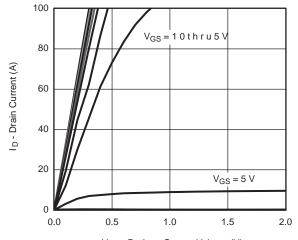
- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 54 °C/W.

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static						L	
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J I _D = - 250 μA		- 31		nc\//04	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		6.5		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
7 0 1 1/1 5 1 0 1	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 30			Α	
		V _{GS} = - 10 V, I _D = - 20 A		0.004	0.005	_	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 15 A		0.006	0.007	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 20 A		97		S	
Dynamic ^b				1			
Input Capacitance	C _{iss}			7050		pF	
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1375			
Reverse Transfer Capacitance	C _{rss}			1215			
Total Gate Charge	Qg	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 20 A		130	250		
				78	130		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$		29			
Gate-Drain Charge	Q _{gd}			37			
Gate Resistance	R _g	f = 1 MHz		1.9		Ω	
Turn-On Delay Time	t _{d(on)}			25	40		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		15	30		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1.0 A, V_{GEN} = - 10 V, R_g = 1 Ω		110	170		
Fall Time	t _f			30	50		
Turn-On Delay Time	t _{d(on)}			110	170	ns -	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		100	150		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		100	150		
Fall Time	t _f			50	75		
Drain-Source Body Diode Characteristi	cs			1			
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			120	^	
Pulse Diode Forward Current ^a	I _{SM}				360	A	
Body Diode Voltage	V _{SD}	I _S = - 5 A		- 0.54	- 1.1	V	
Body Diode Reverse Recovery Time	t _{rr}			50	100	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 3.5 A, dl/dt = 100 A/μs, T _J = 25 °C		65	130	nC	
Reverse Recovery Fall Time	t _a			26			
Reverse Recovery Rise Time	t _b			24		ns	

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$ b. Guaranteed by design, not subject to production testing.

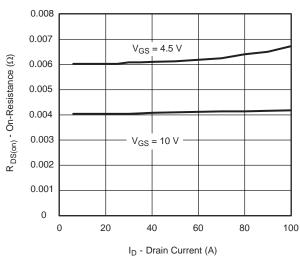
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



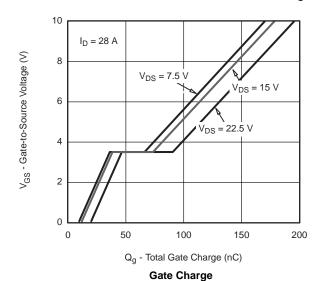


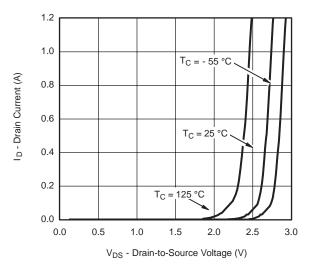
 V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics

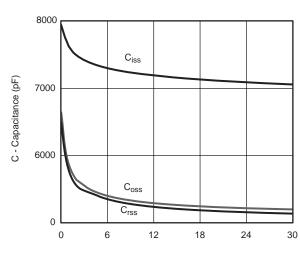


On-Resistance vs. Drain Current and Gate Voltage



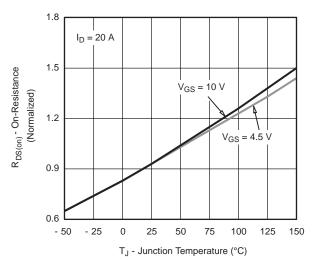


Transfer Characteristics



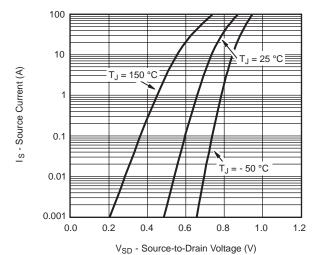
V_{DS} - Drain-to-Source Voltage (V)



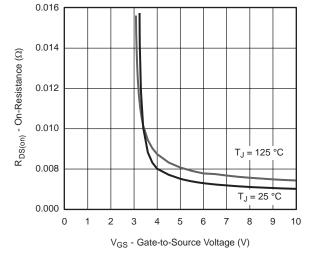


On-Resistance vs. Junction Temperature

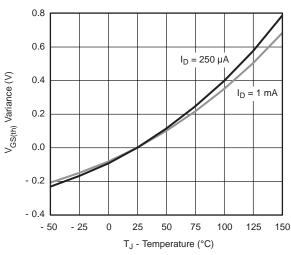




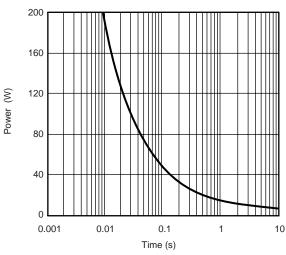
Source-Drain Diode Forward Voltage



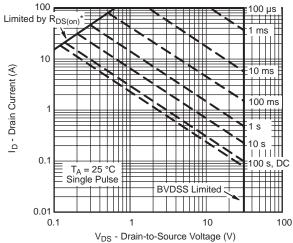
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



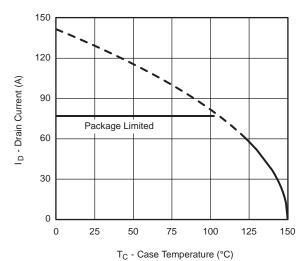
Single Pulse Power, Junction-to-Ambient



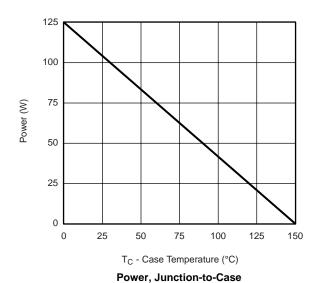
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

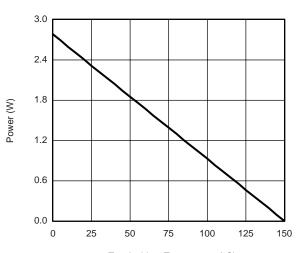
Safe Operating Area, Junction-to-Ambient





Current Derating*

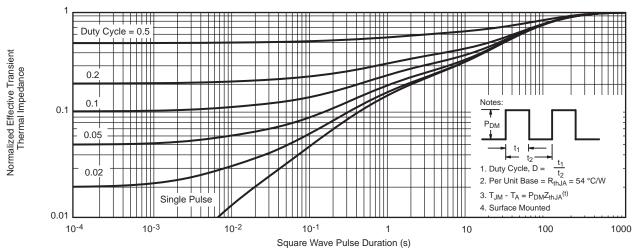




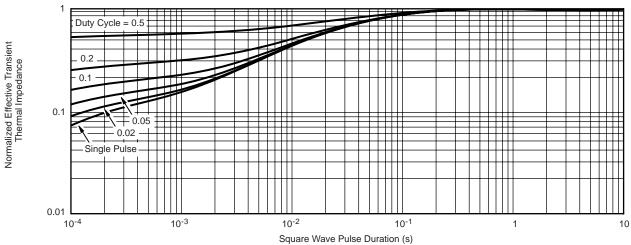
T_A - Ambient Temperature (°C) Power, Junction-to-Ambient

 $^{^*}$ The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





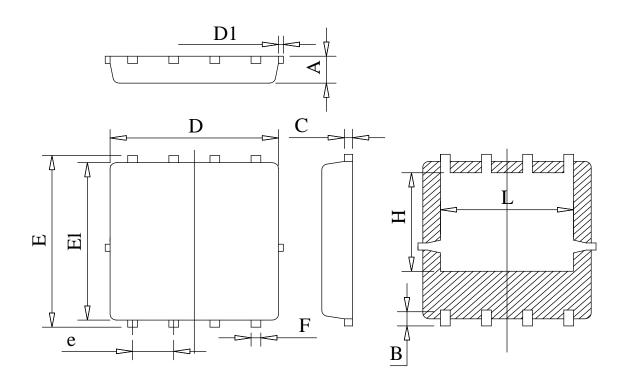
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
C	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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